

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	300.00 +/- 10.00 $\mu$ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00 $\mu$ m	Guaranteed by Process
	7.0	Bow	<40.00 $\mu$ m	ADE to ASTM F534, 20%
	8.0	Warp	<40.00 $\mu$ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	FZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	300.00 +/- 10.00 $\mu$ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	2800- 8000 Ohm-cm	Wafer Vendor
	17.0	Handle Carbon Concentration	<2E16 atoms/cm <sup>3</sup>	Wafer Vendor
	18.0	Handle Oxygen Concentration	<2E16 atoms/cm <sup>3</sup>	Wafer Vendor
	19.0	Frontside Finish	Polished (prime)	Guaranteed by process
	20.0	Backside Finish	Polished	Guaranteed by process
	21.0	Surface Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information